

Thyristor High Voltage, Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	10 A							
V _{DRM} /V _{RRM}	800 V, 1200 V							
V _{TM}	1.4 V							
I _{GT}	60 mA							
TJ	- 40 °C to 125 °C							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC-JESD47
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21
 definition

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5							
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A						
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5							

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	10	٨						
I _{RMS}		16	A						
V _{RRM} /V _{DRM}		800/1200	V						
I _{TSM}		200	А						
V _T	10 A, T _J = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		- 40 to 125	°C						

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-16TTS08SPbF	800	800	10		
VS-16TTS12SPbF	1200	1200	10		

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RoHS

COMPLIANT

HALOGEN

FREE





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ABSOLUTE MAXIMUM RATINGS									
DADAMETED	SYMBOL	TEST CONDITIONS	VALUES						
PARAMETER	STNIDUL	TEST CONDITIONS	TYP. MAX.						
Maximum average on-state current	I _{T(AV)}	$T_{C} = 98 \text{ °C}, 180^{\circ} \text{ conduction, half sine wave}$	10						
Maximum RMS on-state current	I _{RMS}		16						
Maximum peak, one-cycle,		10 ms sine pulse, rated V _{RRM} applied	170						
non-repetitive surge current	ITSM	10 ms sine pulse, no voltage reapplied	200						
Maximum 12t for fusing	12+	10 ms sine pulse, rated V _{RRM} applied	144	A20					
	1-1	10 ms sine pulse, no voltage reapplied	200	A-S					
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	2000	A²√s					
Maximum on-state voltage drop	V _{TM}	10 A, T _J = 25 °C	1.4	V					
On-state slope resistance	r _t	T 125 °C	24.0	mΩ					
Threshold voltage	V _{T(TO)}	1J = 125 C	1.1	V					
Maximum reverse and direct lookage ourrent	1 /1	$T_J = 25 \text{ °C}$	0.5						
Maximum reverse and direct leakage current	IRM/ IDM	$T_J = 125 \text{ °C}$	10						
Holding current	I _H	Anode supply = 6 V, resistive load, initial $I_T = 1 A$	- 100	IIIA					
Maximum latching current	ΙL	Anode supply = 6 V, resistive load	200						
Maximum rate of rise of off-state voltage	dV/dt		500	V/µs					
Maximum rate of rise of turned-on current	dl/dt		150	A/µs					

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0					
Maximum average gate power	P _{G(AV)}		2.0	VV				
Maximum peak positive gate current	+ I _{GM}		1.5	А				
Maximum peak negative gate voltage	- V _{GM}		10	V				
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	90					
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	60	mA				
		Anode supply = 6 V, resistive load, T_J = 125 °C	35					
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	N				
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v				
Maximum DC gate voltage not to trigger V		T 105 °C V Detectualue	0.25	1				
Maximum DC gate current not to trigger	I _{GD}	$i_{\rm J} = 125$ C, $v_{\rm DRM} = nated value$	2.0	mA				

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T 105 %C	4	μs
Typical turn-off time	tq	IJ = 125 C	110	

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THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C				
Soldering temperature	Ts	For 10 s (1.6 mm from case)	240					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C 111				
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount ⁽¹⁾	40	0/11				
Approvimeto weight			2	g				
Approximate weight			0.07	oz.				
Marking davias		Case style D2DAK (SMD 220)	16TTS08S					
warking device		Case Sigie D-PAR (SiviD-220)	16TTS12S					

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994.





Fig. 2 - Current Rating Characteristics



Fig. 3 - On-State Power Loss Characteristics



Fig. 4 - On-State Power Loss Characteristics

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Fig. 5 - Maximum Non-Repetitive Surge Current







Fig. 7 - On-State Voltage Drop Characteristics



Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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VS-16TTS..SPbF Series

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ORDERING INFORMATION TABLE

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Device code	vs-	16	т	т	S	12	S	TRL	PbF		
	1	2	3	4	5	6	(7)	8	9	•	
	1 .	- Visl	hay Sen	niconduc	ctors pro	oduct					
	2	- Cur	Current rating								
	3	- Circ	Circuit configuration:								
		T =	T = Single thyristor								
	4	- Pac	kage:								
		T =	TO-220	AC							
	5	- Тур	e of silio	con:							
		S =	Standa	rd recov	ery rect	ifier		ſ			
	6	- Vol	tage rati	ng: Volt	age cod	le x 100	= V _{RRM}	л — —	08 = 80 12 = 12	V 00 V 00	
	7.	- S=	S = D ² PAK version								
	8 ·	- • No	• None = Tube								
		• TF	RL = Tap	be and re	eel (left	oriented	d)				
		• TI	RR = Ta	pe and r	eel (righ	nt orient	ed)				
	9	- PbF	= = Leac	l (Pb)-fre	ee and I	RoHS c	omplian	ıt			

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

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Outline Dimensions

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D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Ċ 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4)Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 4 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A"

3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES		SYMBOL		MILLIMETERS		INCHES	
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTED	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches



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